

Amendments to the Abstract:

Please amend the abstract as follows.

Presented is a [[A]] method for the production of a plurality of optoelectronic semiconductor chips each having a plurality of structural elements with ~~respectively~~ at least one semiconductor layer. The method involves providing a chip composite base that includes ~~having~~ a substrate and a growth surface. A mask material layer is formed on the growth surface[[,]]. The ~~said~~ mask material layer ~~having~~ includes a multiplicity of windows; ~~most of which have~~ having an average extent of less than or equal to 1 μm . ~~In this case, a~~ A mask material is chosen ~~in such a way so~~ that a semiconductor material of the semiconductor layer that is to be grown in ~~a later method step~~ essentially cannot grow on ~~said~~ the mask material or can grow in a substantially worse manner in comparison with the growth surface. Subsequently, semiconductor layers are deposited essentially simultaneously onto regions of the growth surface that lie within the windows. ~~A further method step is singulation of the~~ The chip composite base with applied material is singulated to form semiconductor chips. ~~An optoelectronic semiconductor component is produced according to the method.~~